Chapter 4

Annealing of implantation damage in SrTiO₃

Annealing conducted to remove the damage induced by the ion implantation process and redistribute the implanted ions into a well defined layer in SrTiO₃ was investigated. A variety of analysis techniques, such as EC, RBS/C and PAC were performed for this purpose. Crucial information about the lattice location of Sr atoms, the crystalline quality and the presence/absence of specific defects in the neighbourhood of implanted atoms, was obtained as a function of annealing temperature from RT to 1300°C. Results are presented and summarized in this chapter.